

# Andrea Canino

## List of Publications by Year in descending order

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32  
papers

365  
citations

1163117

8  
h-index

888059

17  
g-index

32  
all docs

32  
docs citations

32  
times ranked

424  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electroluminescence and transport properties in amorphous silicon nanostructures. Nanotechnology, 2006, 17, 1428-1436.	2.6	68
2	Direct evidence of light confinement and emission enhancement in active silicon-on-insulator slot waveguides. Applied Physics Letters, 2006, 89, 241114.	3.3	62
3	Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus. Electrochemical and Solid-State Letters, 2011, 14, H161.	2.2	39
4	Light emitting devices based on silicon nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 181-187.	2.7	31
5	Structural and electronic characterization of (2,33) bar-shaped stacking fault in 4H-SiC epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	21
6	Raman Characterization of Doped 3C-SiC/Si for Different Silicon Substrates and C/Si Ratios. Materials Science Forum, 0, 645-648, 255-258.	0.3	18
7	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. Surface Science, 2010, 604, 939-942.	1.9	17
8	Reduction of the Surface Density of Single Shockley Faults by TCS Growth Process. Materials Science Forum, 0, 679-680, 67-70.	0.3	12
9	Optical investigation of bulk electron mobility in 3C-SiC films on Si substrates. Applied Physics Letters, 2010, 97, 142103.	3.3	11
10	Numerical Modeling of Bifacial PV String Performance: Perimeter Effect and Influence of Uniaxial Solar Trackers. Energies, 2020, 13, 869.	3.1	10
11	Study of the Evolution of Basal Plane Dislocations during Epitaxial Growth: Role of the Surface Kinetics. Materials Science Forum, 2010, 645-648, 539-542.	0.3	8
12	Systematic First Principles Calculations of the Effects of Stacking Fault Defects on the 4H-SiC Band Structure. Materials Science Forum, 0, 645-648, 283-286.	0.3	8
13	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. Materials Science Forum, 0, 740-742, 229-234.	0.3	8
14	Single Shockley Faults Enlargement during Micro-Photoluminescence Defects Mapping. Materials Science Forum, 0, 645-648, 555-558.	0.3	7
15	Advanced Stress Analysis by Micro-Structures Realization on High Quality Hetero-Epitaxial 3C-SiC for MEMS Application. Materials Science Forum, 2011, 679-680, 133-136.	0.3	7
16	Fast Growth Rate Epitaxy by Chloride Precursors. Materials Science Forum, 2013, 740-742, 167-172.	0.3	5
17	Correlation between macroscopic and microscopic stress fields: Application to the 3C-SiC/Si heteroepitaxy. Journal of Materials Research, 2013, 28, 104-112.	2.6	5
18	Publisher's Note: Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus [Electrochem. Solid-State Lett., 14, H161 (2011)]. Electrochemical and Solid-State Letters, 2011, 14, S3.	2.2	4

#	ARTICLE	IF	CITATIONS
19	Raman Study of Bulk Mobility in 3C-SiC Heteroepitaxy. Materials Science Forum, 0, 679-680, 221-224.	0.3	4
20	Large area optical characterization of 3 and 4 inches 4H-SiC wafers. Thin Solid Films, 2012, 522, 30-32.	1.8	4
21	New approaches for enhancing light emission from Er-based materials and devices. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 891-898.	2.7	3
22	Single Shockley Faults Evolution Under UV Optical Pumping. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	3
23	Extended Characterization of the Stress Fields in the Heteroepitaxial Growth of 3C-SiC on Silicon for Sensors and Device Applications. Materials Science Forum, 0, 717-720, 517-520.	0.3	3
24	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. Materials Science Forum, 2012, 717-720, 113-116.	0.3	2
25	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. Materials Science Forum, 2012, 717-720, 149-152.	0.3	2
26	3C-SiC Growth on (001) Si Substrates by Using a Multilayer Buffer. Materials Science Forum, 0, 740-742, 263-266.	0.3	2
27	Advanced Residual Stress Analysis on the Heteroepitaxial Growth of 3C-SiC/Si for MEMS Application. ECS Transactions, 2011, 35, 123-131.	0.5	1
28	Light emitting devices based on Si nanoclusters: the integration with a photonic crystal and electroluminescence properties. Optoelectronics Letters, 2007, 3, 321-325.	0.8	0
29	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. Electrochemical and Solid-State Letters, 2011, 14, H457.	2.2	0
30	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. ECS Transactions, 2011, 35, 117-122.	0.5	0
31	Stress Relaxation Study in 3C-SiC Microstructures by Micro-Raman Analysis and Finite Element Modeling. Materials Science Forum, 0, 740-742, 673-676.	0.3	0
32	Reversible Efficiency Variation of Tandem Amorphous/Microcrystalline Si Photovoltaic Modules in Outdoor Operation. Energies, 2019, 12, 2876.	3.1	0